

2N3998  
N-P-N EPITAXIAL PLANAR SILICON POWER TRANSISTOR

\* electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN MAX		UNIT
$V_{(BR)CEO}$ Collector-Emitter Breakdown Voltage	$I_C = 50 \text{ mA}, I_B = 0$ , See Note 5	80		V
$I_{CEO}$ Collector Cutoff Current	$V_{CE} = 60 \text{ V}, I_B = 0$	10		$\mu\text{A}$
$I_{CES}$ Collector Cutoff Current	$V_{CE} = 90 \text{ V}, V_{BE} = 0$	5		$\mu\text{A}$
	$V_{CE} = 90 \text{ V}, V_{BE} = 0, T_C = 150^\circ\text{C}$	50		
$I_{ESO}$ Emitter Cutoff Current	$V_{EB} = 5 \text{ V}, I_C = 0$	0.5		$\mu\text{A}$
	$V_{EB} = 8 \text{ V}, I_C = 0$	10		
$h_{FE}$ Static Forward Current Transfer Ratio	$V_{CE} = 2 \text{ V}, I_C = 50 \text{ mA}$	30		
	$V_{CE} = 2 \text{ V}, I_C = 1 \text{ A}$ , See Note 5	40	120	
	$V_{CE} = 5 \text{ V}, I_C = 5 \text{ A}$ , See Note 5	1.5		
	$V_{CE} = 2 \text{ V}, I_C = 1 \text{ A}, T_C = -55^\circ\text{C}$ , See Note 5	10		
$V_{BE}$ Base-Emitter Voltage	$I_B = 100 \text{ mA}, I_C = 1 \text{ A}$ , See Note 5	0.6	1.2	V
	$I_B = 500 \text{ mA}, I_C = 5 \text{ A}$ , See Note 5	1.6		
$V_{CE(sat)}$ Collector-Emitter Saturation Voltage	$I_B = 100 \text{ mA}, I_C = 1 \text{ A}$ , See Note 5	0.25		V
	$I_B = 500 \text{ mA}, I_C = 5 \text{ A}$ , See Note 5	2		
$ h_{fe} $ Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}, f = 10 \text{ Mc/s}$	4		
$C_{obs}$ Common-Base Open-Circuit Output Capacitance	$V_{CE} = 10 \text{ V}, I_E = 0, f = 1 \text{ Mc/s}$	150		pF

NOTE 5: This parameter must be measured using pulse techniques:  $I_p = 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

\* thermal characteristics

PARAMETER	MAX	UNIT
$\theta_{J-C}$ Junction-to-Case Thermal Resistance	3.33	deg/W
$\theta_{J-A}$ Junction-to-Free-Air Thermal Resistance	87.5	deg/W

\* switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS†	MAX	UNIT
$t_{on}$ Turn-On Time	$I_C = 1 \text{ A}, I_{B(1)} = 100 \text{ mA}, I_{B(2)} = -100 \text{ mA}, V_{BE(off)} = -3.7 \text{ V}, R_L = 20 \Omega$ , See Figure 1	0.3	$\mu\text{s}$
$t_{off}$ Turn-Off Time		1.5	

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

\* indicates JEDEC registered data.

\* mechanical data

